

MARKED-UP COPY OF AMENDMENTS

IN RE APPLICATION OF: :
ATSUSHI SHIOTA ET AL. : GROUP ART UNIT: 1712
SERIAL NO: 09/770,289 :
FILED: JANUARY 29, 2001 : EXAMINER: FEELY, M.
FOR: PROCESS FOR PRODUCING
SILICA-BASED FILM, SILICA-
BASED FILM, INSULATING FILM,
AND SEMICONDUCTOR DEVICE

AMENDMENT AFTER FINAL REJECTION

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

In response to the Final Rejection dated June 24, 2002, please amend the application identified above as follows (marked-up copy of amendments attached):

IN THE CLAIMS

Please cancel Claim 16 without prejudice to or disclaimer of the subject matter therein.

Please amend Claim 1 as follows:

1. (Two Times Amended) A process for producing a silica-based film, the process comprising irradiating a film comprising at least one siloxane compound with electron beams at an irradiation dose of from 1 to [500] 200 $\mu\text{C}/\text{cm}^2$ to thereby convert the film into a film having a dielectric constant of 3 or lower and having silicon carbide bonds represented by Si-